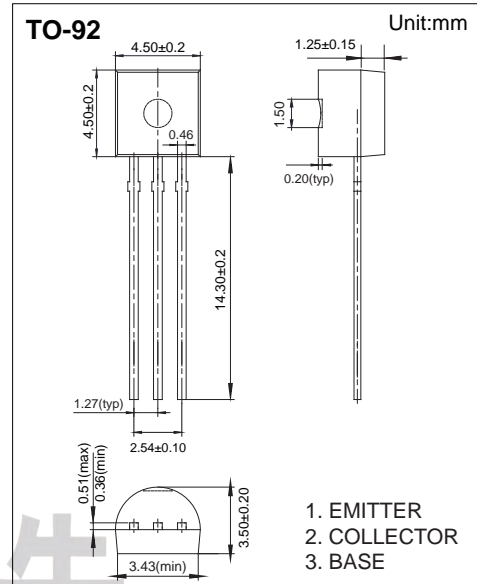


PNP Transistors A733

■ Features

- Power dissipation: $P_C=0.25W$
- Collector current: $I_C=0.1A$



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-60	V
Collector - Emitter Voltage	V_{CEO}	-50	
Emitter - Base Voltage	V_{EBO}	-5	
Collector Current - Continuous	I_C	-100	mA
Collector Power Dissipation	P_C	250	mW
Junction Temperature	T_J	150	°C
Storage Temperature	T_{stg}	-55 to 150	

Transistor

PNP Transistors A733

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CB0}	$I_C = -50 \mu\text{A}, I_E = 0$	-60			V
Collector- emitter breakdown voltage	V_{CEO}	$I_C = -1 \text{mA}, I_B = 0$	-50			
Emitter - base breakdown voltage	V_{EB0}	$I_E = -50 \mu\text{A}, I_C = 0$	-5			
Collector cut-off current	I_{CBO}	$V_{CB} = -60 \text{V}, I_E = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5 \text{V}, I_C = 0$			-0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100 \text{mA}, I_B = -10 \text{mA}$			-0.3	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = -100 \text{mA}, I_B = -10 \text{mA}$			-1.1	
Base-emitter voltage	V_{BE}	$V_{CE} = -6 \text{V}, I_C = -1 \text{mA}$	-0.58		-0.68	
DC current gain	h_{FE}	$V_{CE} = -6 \text{V}, I_C = -1 \text{mA}$	90		600	
Noise figure	NF	$V_{CE} = -6 \text{V}, I_C = -0.3 \text{mA}, f = 100 \text{Hz}, R_G = 10 \text{k}\Omega$			20	dB
Collector output capacitance	C_{ob}	$V_{CB} = -10 \text{V}, I_E = 0, f = 1 \text{MHz}$			6	pF
Transition frequency	f_T	$V_{CE} = -6 \text{V}, I_C = -10 \text{mA}$	100			MHz

■ Classification of h_{FE}

Rank	R	Q	P	K
Range	90-180	135-270	200-400	300-600